

21st RD50 Workshop (CERN)

Thursday, 15 November 2012

Detector Characterization and Simulations (09:00 - 15:30)

-Conveners: Eckhart Fretwurst; Vladimir Eremin

time	[id] title	presenter
09:00	[3] Irradiation study on diodes of different silicon materials for the CMS tracker upgrade	ERFLE, Joachim
09:15	[24] Impact of proton irradiations on the electrical properties of n-type Si-diodes	Ms NEUBÜSER, Coralie
09:30	[50] Measurements on 800 MeV proton irradiated diodes (moved from Wednesday!)	JUNKES, Alexandra
09:40	[32] First investigation of silicon microstrips for the CMS tracker upgrade using edge-TCT	FERNANDEZ GARCIA, Marcos
10:00	[8] Temperature dependence of the bulk current in Si	CHILINGAROV, Alexandre
10:20	[15] Charge collection studies on heavily irradiated diodes from the RD50 multiplication run (an update)	KRAMBERGER, Gregor
10:40	Coffee Break	
11:10	[31] Annealing of Heavy Irradiated n-on-p Diodes at Temperatures 20°, 40°, 60° and 80°C	MIKESTIKOVA, Marcela
11:30	[10] TCT measurements with irradiated strip detectors	MANDIC, Igor
11:50	[7] Electrical characterisation of heavily irradiated microstrip sensors	Dr CHILINGAROV, Alexandre
12:10	[0] Simulation of irradiated silicon p-bulk sensors	BOMBEN, Marco
12:30	[21] Simulation of electric field profile in Si irradiated detectors with a consideration of carrier generation parameters	Dr VERBITSKAYA, Elena
12:50	Lunch	
14:00	[30] Simulation of an effective 2-trap radiation damage model	EBER, Robert
14:20	[35] Double Electric field Peak Simulation of Irradiated Detectors Using TCAD tools	BHARDWAJ, Ashutosh
14:40	[45] Simulation of Double Junction using Synopsys TCAD	MOLL, Michael
15:00	[29] Discussion on Detector Characterization and Simulations	FRETWURST, Eckhart EREMIN, Vladimir